

In the Claims

Claims 1-26 (Canceled).

27 (Currently Amended). A method of forming a deposit in making semiconductor devices comprising the steps of:

forming at least one annular opening in a plate creating an inner member inward of said opening and an outer member outward of said opening; and
maintaining a physical connection between said inner and outer members.

28 (Currently Amended). The method stencil of claim 27 having a thickness of from about 3 to about 10 mils.

29 (Currently Amended). The method stencil of claim 28 wherein said annular opening has a radial width of about 1 mil.

Claims 30-33 (Canceled).